Question Paper Code: AEC001

## FOR LINE NO.

INSTITUTE OF AERONAUTICAL ENGINEERING

(Autonomous)

Four Year B.Tech III Semester End Examinations (Regular) - November, 2018

Regulation: IARE – R16

ELECTRONIC DEVICES AND CIRCUITS

Time: 3 Hours

 $(Common to ECE \mid EEE)$ 

Max Marks: 70

## Answer ONE Question from each Unit All Questions Carry Equal Marks All parts of the question must be answered in one place only

## $\mathbf{UNIT} - \mathbf{I}$

1.	(a)	Derive the expression for diode equation with neat sketches.	[7M]
	(b)	$\operatorname{Explain}$ semi-conductors, insulators and metals classification using energy band diagrams.	[7M]
2.	(a)	Explain how Zener diode can act as a Voltage Regulator.	[7M]
	(b)	How a PN junction diode works? Sketch and explain the V-I characteristics of PN diode works neat diagram.	with a [ <b>7M</b> ]
$\mathbf{UNIT} - \mathbf{II}$			
3.	(a)	Draw a neat diagram and explain the operation of full wave bridge rectifier.	[7M]
	(b)	List the types of filters used in rectification. Derive the expression for ripple factor using C- $[7{\rm M}]$	-filter.
4.	(a)	<ul><li>What is Rectification efficiency? Derive expression for the following</li><li>i. Half wave rectifier</li><li>ii. Full wave rectifier</li></ul>	[7M]
	(b)	Explain the construction and working of Tunnel diode.	[7M]
$\mathbf{UNIT} - \mathbf{III}$			
5.	(a)	Describe the working principle of MOSFET in enhancement mode.	[7M]
	(b)	Compare CE, CB and CC configurations. Distinguish between BJT and FET devices.	[7M]
6.	(a)	Compare and contrast construction of JFET with MOSFET. Sketch the circuit symbols MOSFETs	of all [ <b>7M</b> ]
	(b)	Sketch the drain characteristics of a n-channel JFET and Explain it.	[7M]
$\mathbf{UNIT} - \mathbf{IV}$			
7.	(a)	Sketch the selfbias circuit with BJT. Derive expressions for stability factor "S".	[7M]
	(b)	What is stability factor? Discuss the factors that cause instability of biasing circuit.	[7M]
8.	(a)	Discuss the need for biasing a transistor. Illustrate the DC load line analysis of BJT.	[7M]

(b) Sketch and illustrate various biasing techniques of JFET.

[7M]

## $\mathbf{UNIT}-\mathbf{V}$

- 9. (a) Give the complete analysis of CB transistor amplifier circuit using h-parameters. Derive expressions for the current gain, voltage gain, input impedance and output admittance. [7M]
  - (b) Sketch the h-parameters equivalent circuit for a common emitter amplifier and derive the expression for  $A_i$ ,  $R_i$ ,  $A_v$ . [7M]
- 10. (a) Describe the analysis of generalized transistor amplifier circuit using h-parameter model. Derive the equation for input impedance, voltage gain and output admittance. [7M]
  - (b) Derive the expressions for  $Z_i$ ,  $Z_o$  and  $A_v$  for common source J-FET amplifier. [7M]

 $-\circ\circ\bigcirc\circ\circ-$